
2SK2554

Silicon N-Channel MOS FET

HITACHI

ADE-208-359 D
5th. Edition

Application

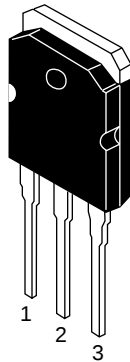
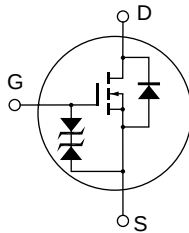
High speed power switching

Features

- Low on-resistance
- $R_{DS(on)} = 4.5 \text{ m}\Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline

TO-3P



1. Gate
2. Drain
(Flange)
3. Source

Absolute Maximum Ratings (Ta = 25°C)

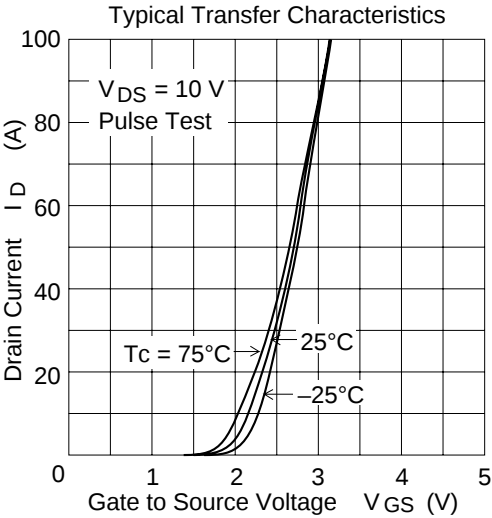
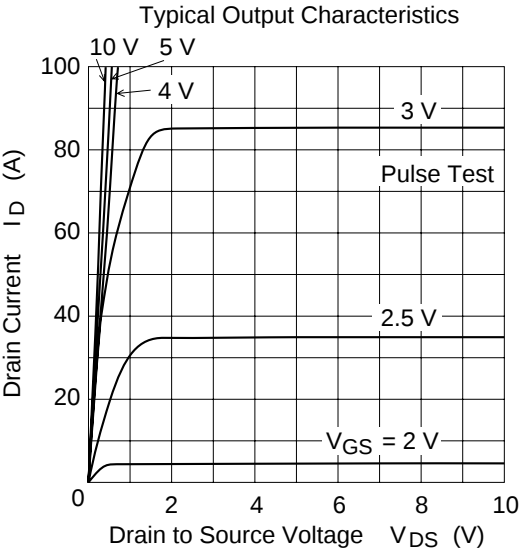
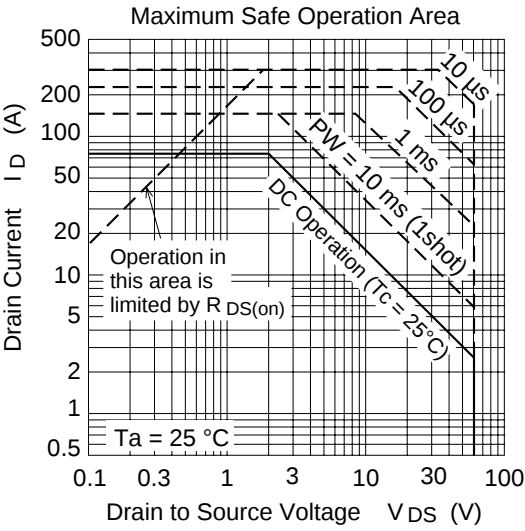
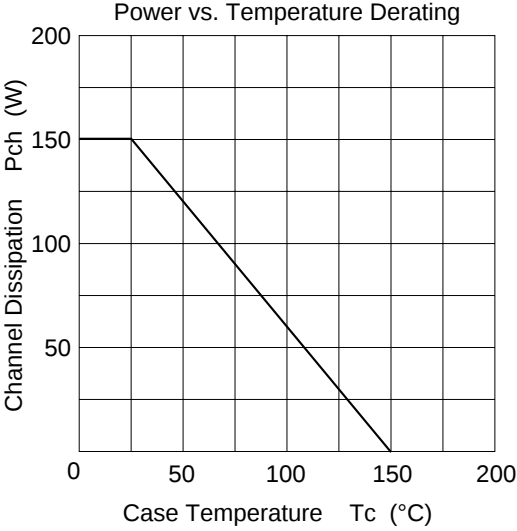
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	75	A
Drain peak current	I _{D(pulse)} ^{*1}	300	A
Body to drain diode reverse drain current	I _{DR} ^{*2}	75	A
Avalanche current	I _{AP} ^{*3}	50	A
Avalanche energy	E _{AR} ^{*3}	214	mJ
Channel dissipation	Pch ^{*2}	150	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg ≥ 50 Ω

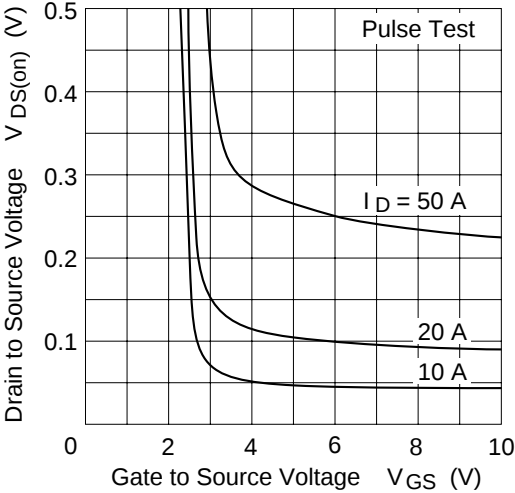
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	100	μA	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	4.5	6	mΩ	$I_D = 40 \text{ A}$ $V_{GS} = 10 \text{ V}^{*1}$
		—	5.8	10	mΩ	$I_D = 40 \text{ A}$ $V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	50	80	—	S	$I_D = 40 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	7700	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	4100	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	760	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	60	—	ns	$I_D = 40 \text{ A}$
Rise time	t_r	—	420	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	1200	—	ns	$R_L = 0.75 \text{ } \Omega$
Fall time	t_f	—	900	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_F = 75 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	105	—	ns	$I_F = 75 \text{ A}$, $V_{GS} = 0$ $diF / dt = 50 \text{ A} / \mu\text{s}$

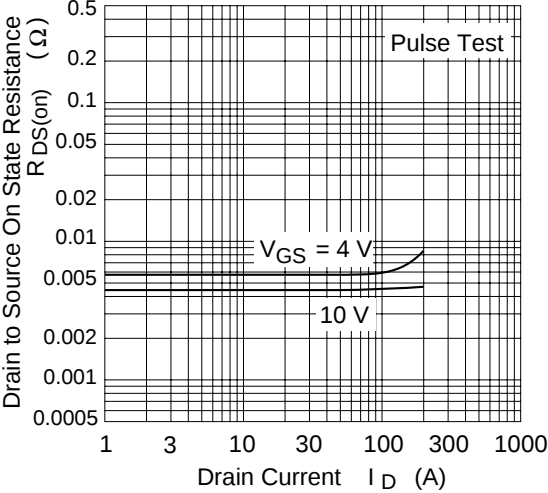
Note: 1. Pulse Test



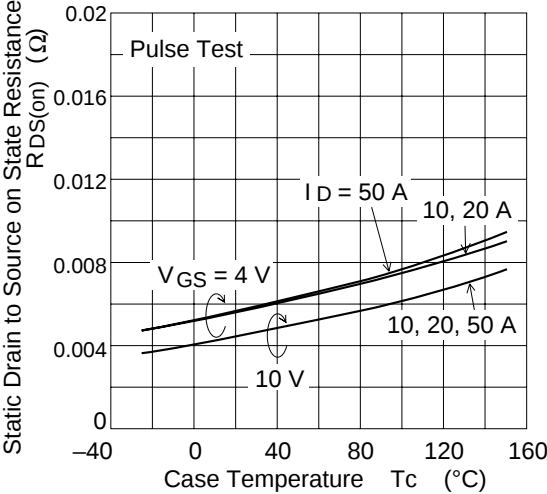
Drain to Source Saturation Voltage vs.
Gate to Source Voltage



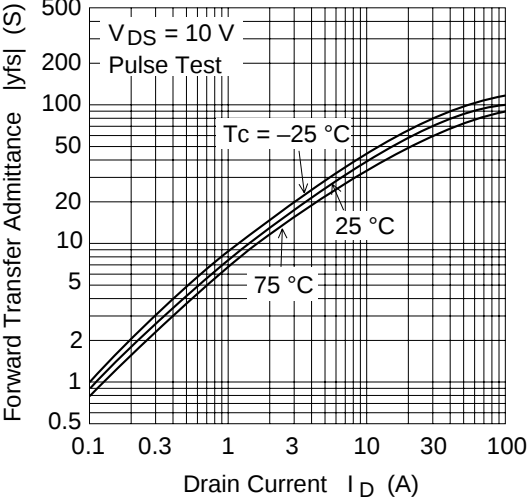
Static Drain to Source on State Resistance
vs. Drain Current

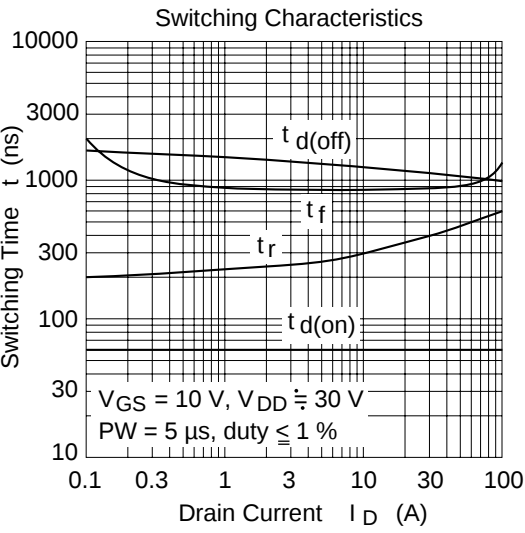
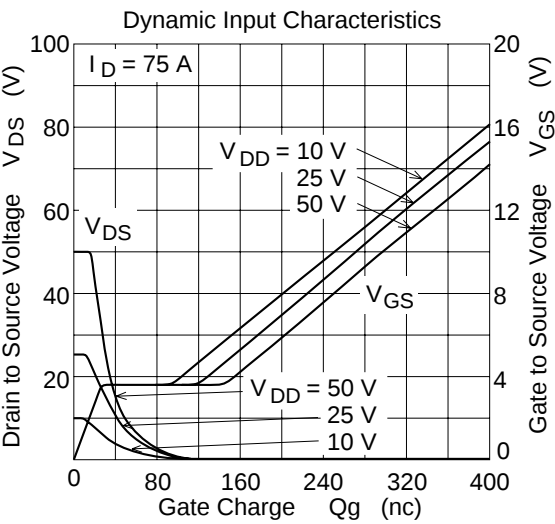
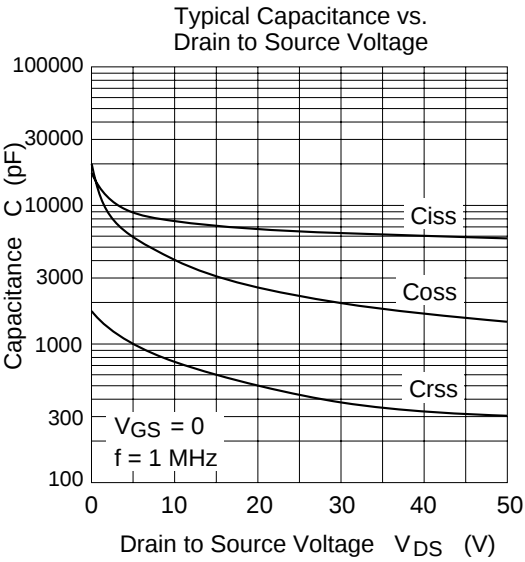
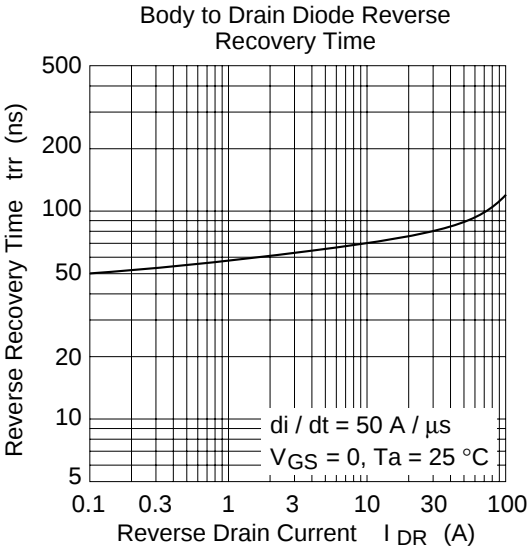


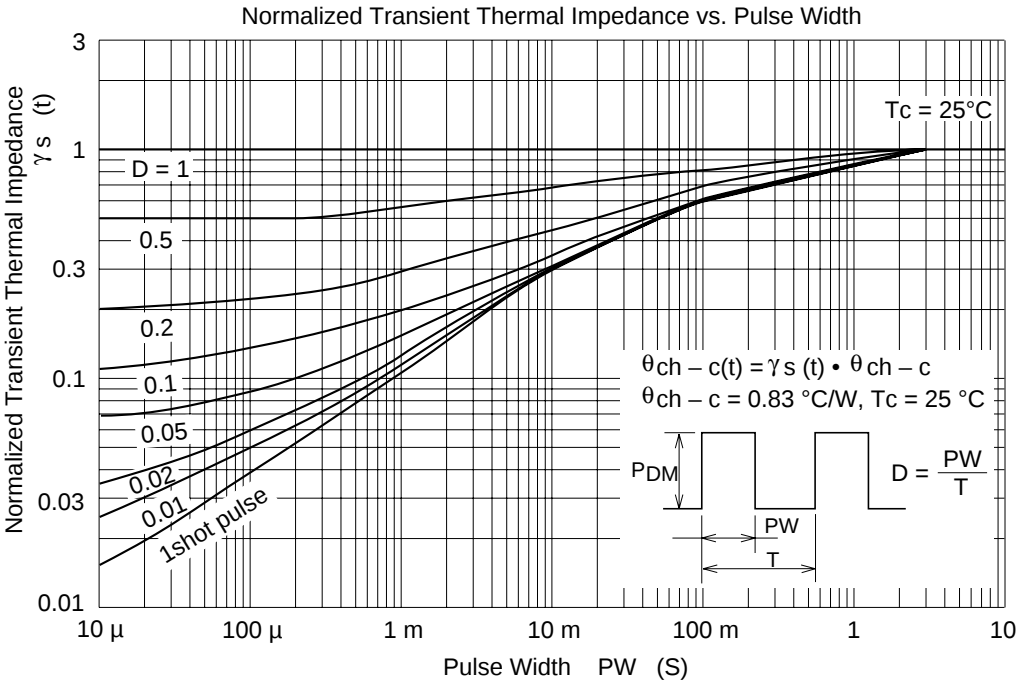
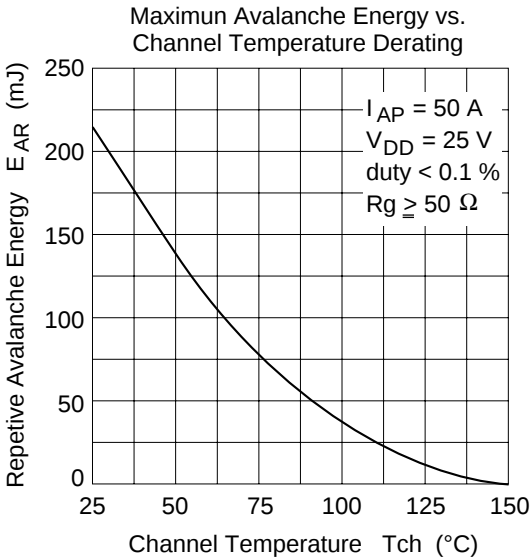
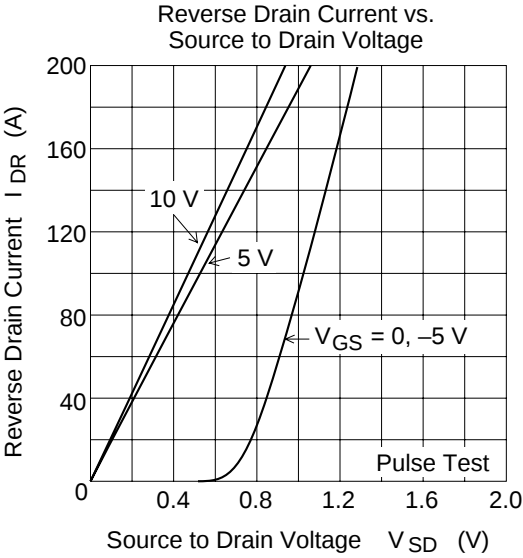
Static Drain to Source on State Resistance
vs. Temperature



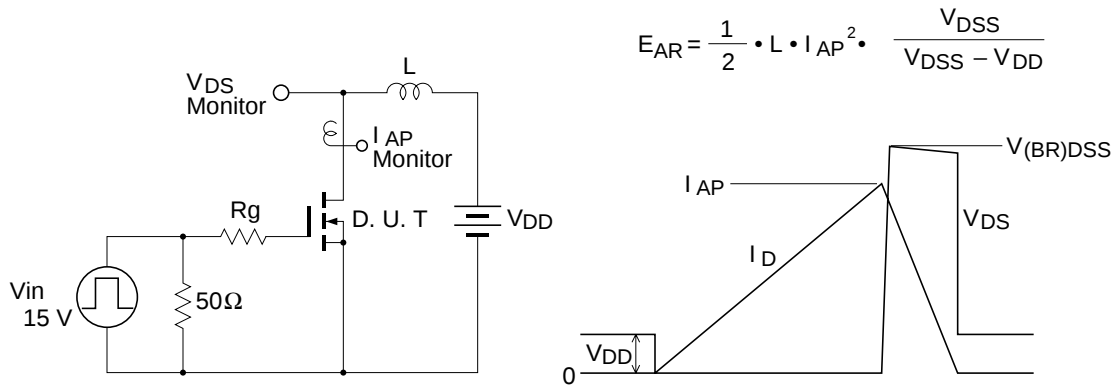
Forward Transfer Admittance vs.
Drain Current



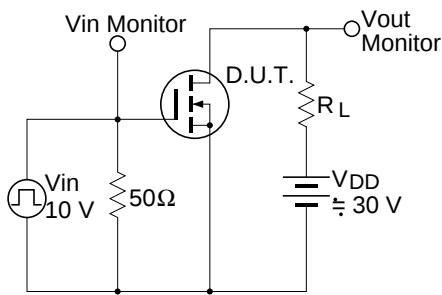




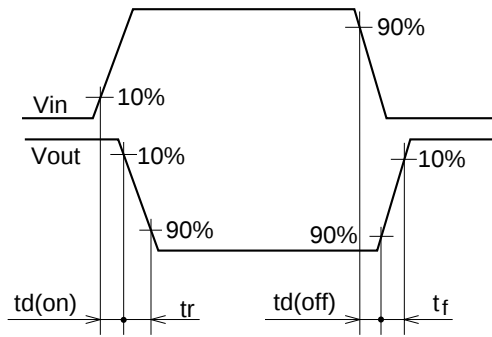
Avalanche Test Circuit and Waveform



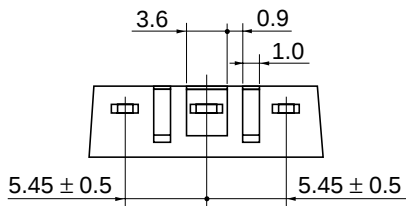
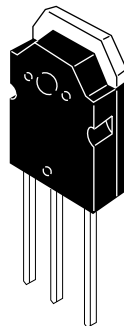
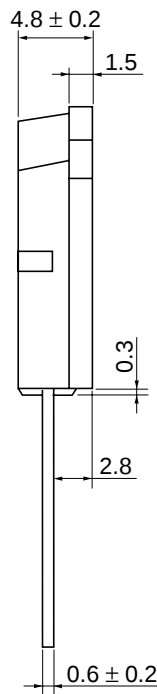
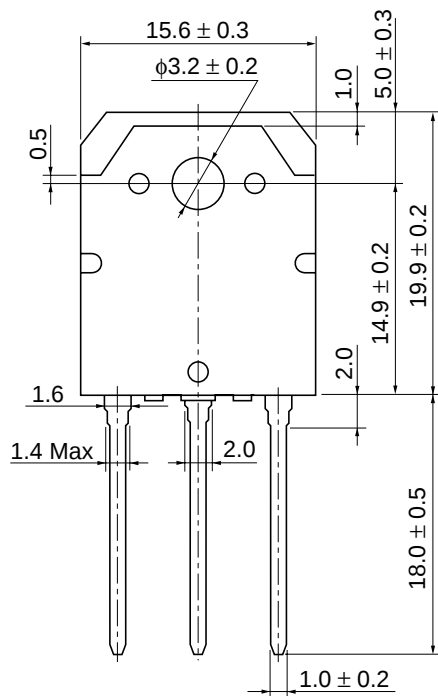
Switching Time Test Circuit



Waveform



Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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